(Supplemental)

High Deposition Rate TiO PEALD Process for Semiconductor Industry

Sungbae Kim, Yeahyun Gu, Hyunchul Kim, and Hyungjoo Shin

ASM International N.V., Hwasung-si, Gyunggi-do, Republic of Korea

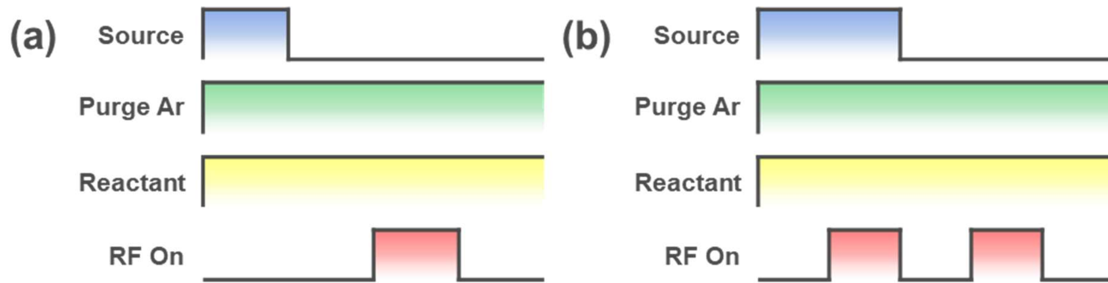

Figure 1. Process sequence comparison (a) Conventional ALD (b) High Dep. Rate ALD

	Conventional ALD	**High Dep. Rate ALD**
Thickness Map		
Thickness (Å)	**1830**	**1790**
Non-Uniformity (%)	**0.33**	**0.28**
Refractive Index	**2.380**	**2.310**
Deposition Rate (Å/sec)	**0.34**	**0.94**

Table 1. Comparison of thin film characteristics of the Conventional ALD and the High Dep. Rate ALD